

**TYPE: 34063n.d.2**

CHIP APPEARANCE		CHIP SIZE		1,18 × 1,27 mm						
		CHIP THICKNESS		$460 \pm 20 \mu\text{m}$						
BONDING PAD DIMENSION	1a 1b	SWITCH COLLECTOR	$90 \times 90 \mu\text{m}$							
	2a 2b	SWITCH EMITTER	$90 \times 90 \mu\text{m}$							
	3	TIMING CAPACITOR	$90 \times 90 \mu\text{m}$							
	4	GROUND	$90 \times 90 \mu\text{m}$							
	5	COMPARATOR INVERTING INPUT	$90 \times 90 \mu\text{m}$							
	6	V <sub>CC</sub>	$90 \times 90 \mu\text{m}$							
	7	I <sub>pk</sub> SENSE	$90 \times 90 \mu\text{m}$							
	8	DRIVER COLLECTOR	$90 \times 90 \mu\text{m}$							
	SCRIBE LINE WIDTH		96 $\mu\text{m}$							
TOP METAL		Al								
BACK METAL		—								
WAFER SIZE		100 mm								

**ELECTRICAL CHARACTERISTICS**

(V<sub>CC</sub> = 5.0 V, T<sub>A</sub> = T<sub>low</sub> to T<sub>high</sub>, unless otherwise specified.)

Characteristics	Symbol	Min	TYP	Max	Unit
<b>OSCILLATOR</b>					
Frequency (V <sub>pin5</sub> = 0 V, C <sub>T</sub> = 1.0 nF, T <sub>A</sub> = 25°C)	f <sub>osc</sub>	24	33	42	kHz
Charge Current (V <sub>CC</sub> = 5.0V to 40V, T <sub>A</sub> = 25°C)	I <sub>chg</sub>	24	35	42	$\mu\text{A}$
Discharge Current (V <sub>CC</sub> = 5.0V to 40V, T <sub>A</sub> = 25°C)	I <sub>dischg</sub>	140	220	260	$\mu\text{A}$
Discharge to Charge Current Ratio (Pin 7 to V <sub>CC</sub> , T <sub>A</sub> = 25°C)	I <sub>dischg</sub> / I <sub>chg</sub>	5.2	6.5	7.5	—
Current Limit Sense Voltage (I <sub>chg</sub> = I <sub>dischg</sub> , T <sub>A</sub> = 25°C)	V <sub>Ipk(sense)</sub>	250	300	350	mV
<b>OUTPUT SWITCH (NOTE 2)</b>					
Saturation Voltage, Darlington Connection (I <sub>sw</sub> = 1.0 A, Pins 1, 8 connected)	V <sub>CE(sat)</sub>	—	1.0	1.3	V
Saturation Voltage, Darlington Connection (I <sub>sw</sub> = 1.0 A, R <sub>din8</sub> = 82Ω to V <sub>CC</sub> , Forced $\beta \approx 20$ )	V <sub>CE(sat)</sub>	—	0.45	0.7	V
DC Current Gain (I <sub>sw</sub> = 1.0 A, V <sub>CE</sub> = 5.0 V, T <sub>A</sub> = 25°C)	h <sub>FE</sub>	50	75	—	—
Collector Off-State Current (V <sub>CE</sub> = 40 V)	I <sub>C(off)</sub>	—	40	100	$\mu\text{A}$
<b>COMPARATOR</b>					
Threshold Voltage (T <sub>A</sub> =25°C) (T <sub>A</sub> =T <sub>low</sub> to T <sub>high</sub> )	V <sub>th</sub>	1.225 1.21	1.25	1.275 1.29	V
Threshold Voltage Line Regulation (Vcc=3.0 V to 40 V)	Reg <sub>line</sub>	—	1.4	5.0	mV
Input Bias Current (Vin=0 V)	I <sub>IB</sub>	—	-20	-400	nA
<b>TOTAL DEVICE</b>					
Supply Current (Vcc = 5.0 V to 40 V, C <sub>T</sub> = 1.0 nF, Pin 7 = V <sub>CC</sub> , V <sub>pin5</sub> > V <sub>th</sub> , Pin 2 = Gnd, remaining pins open)	I <sub>cc</sub>	—	—	4.0	mA

**NOTES :**

1. Maximum package power dissipation limits must be observed.
2. Low duty cycle pulse techniques are used during test to maintain junction temperature as close to ambient temperature as possible.

## **ABSOLUTE MAXIMUM RATINGS**

<b>Rating</b>	<b>Symbol</b>	<b>Value</b>	<b>Unit</b>
Power Supply Voltage	$V_{CC}$	40	Vdc
Comparator Input Voltage Range	$V_{IR}$	-0.3 to +40	Vdc
Switch Collector Voltage	$V_{C(switch)}$	40	Vdc
Switch Emitter Voltage ( $V_{PIN1} = 40$ V)	$V_{E(switch)}$	40	Vdc
Switch Collector to Emitter Voltage	$V_{CE(switch)}$	40	Vdc
Driver Collector Voltage	$V_{C(driver)}$	40	Vdc
Driver Collector Current (Note 1)	$I_{C(driver)}$	100	mA
Switch Current	$I_{SW}$	1.5	A
Operating Junction Temperature	$T_J$	+150	°C
Operating Ambient Temperature Range	$T_A$	0 to +70	°C
Storage Temperature Range	Tstg	-65 to +150	°C